

Hong-Yu Yu

List of Publications by Year in descending order

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146
papers

4,461
citations

136950

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118850

62
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148
all docs

148
docs citations

148
times ranked

5693
citing authors

#	ARTICLE	IF	CITATIONS
1	Reply to the "Comment on "High-temperature superconductivity in transition metallic hydrides MH ₁₁ (M = Mo, W, Nb, and Ta) under high pressure" by X. Zheng and J. Zheng, <i>Phys. Chem. Chem. Phys.</i> , 2022, 24 , DOI: 10.1039/D1CP01474A. <i>Physical Chemistry Chemical Physics</i> , 2022, 24 , 1898-1899.	2.8	1
2	Atomic layer etching technique for InAlN/GaN heterostructure with AlN etch-stop layer. <i>Materials Science in Semiconductor Processing</i> , 2022, 143 , 106544.	4.0	7
3	Normally-OFF AlGaIn/GaN MIS-HEMTs With Low R _{ON} and V _{th} Hysteresis by Functioning <i>In-situ</i> SiN _x in Regrowth Process. <i>IEEE Electron Device Letters</i> , 2022, 43 , 529-532.	3.9	14
4	Carbon monoxide detection down to ppb-level realized by O ₂ plasma treated TiO ₂ -gated AlGaIn/GaN HEMT sensor. <i>Sensors and Actuators B: Chemical</i> , 2022, 359 , 131556.	7.8	3
5	p-GaN Gate HEMTs With 10.6 V Maximum Gate Drive Voltages by Mg Doping Engineering. <i>IEEE Transactions on Electron Devices</i> , 2022, 69 , 2282-2286.	3.0	8
6	Low trap density of oxygen-rich HfO ₂ /GaN interface for GaN MIS-HEMT applications. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2022, 40 , .	1.2	4
7	Physical factors controlling the diverse seismogenic behavior of fluid injections in Western Canada. <i>Earth and Planetary Science Letters</i> , 2022, 589 , 117555.	4.4	6
8	Complex spin Hamiltonian represented by an artificial neural network. <i>Physical Review B</i> , 2022, 105 , .	3.2	8
9	The Atomic Layer Etching Technique with Surface Treatment Function for InAlN/GaN Heterostructure. <i>Crystals</i> , 2022, 12 , 722.	2.2	2
10	A Method to Determine Dielectric Model Parameters for Broadband Permittivity Characterization of Thin Film Substrates. <i>IEEE Transactions on Electromagnetic Compatibility</i> , 2021, 63 , 229-236.	2.2	4
11	Detection of microRNA ^{33a} in serum, urine and renal tissue of patients with IgA nephropathy. <i>Experimental and Therapeutic Medicine</i> , 2021, 21 , 205.	1.8	2
12	Buried Interfaces in Halide Perovskite Photovoltaics. <i>Advanced Materials</i> , 2021, 33 , e2006435.	21.0	214
13	Recent Advances in GaN-Based Power HEMT Devices. <i>Advanced Electronic Materials</i> , 2021, 7 , 2001045.	5.1	86
14	Spin Hamiltonians in Magnets: Theories and Computations. <i>Molecules</i> , 2021, 26 , 803.	3.8	33
15	A Study on the Largest Hydraulic Fracturing Induced Earthquake in Canada: Numerical Modeling and Triggering Mechanism. <i>Bulletin of the Seismological Society of America</i> , 2021, 111 , 1392-1404.	2.3	20
16	Performance of InGaIn green light-emitting diodes with on-chip photodetectors based on wire-bonding and flip-chip configurations. <i>Applied Optics</i> , 2021, 60 , 2599.	1.8	5
17	Formation of ultra-high-resistance Au/Ti/p-GaN junctions and the applications in AlGaIn/GaN HEMTs. <i>AIP Advances</i> , 2021, 11 , 045207.	1.3	1
18	Determination of the Gate Breakdown Mechanisms in p-GaN Gate HEMTs by Multiple-Gate-Sweep Measurements. <i>IEEE Transactions on Electron Devices</i> , 2021, 68 , 1518-1523.	3.0	11

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19	Achieving A Low Contact Resistivity of $0.11 \hat{\text{I}} \hat{\text{O}} \hat{\text{A}} \hat{\text{m}} \text{m}$ for Ti ₅ Al ₁ /TiN S/D Contact on Al _{0.2} Ga _{0.8} N/ AlN/GaN Structure without Barrier Recess. , 2021, , .		1
20	Nonuniform grid upscaling method for geologic model of oil reservoir: A case study of the W block in the northern part of the Songliao Basin. Interpretation, 2021, 9, T443-T452.	1.1	0
21	Dielectric screening in perovskite photovoltaics. Nature Communications, 2021, 12, 2479.	12.8	88
22	Study of bilayer Al ₂ O ₃ /in-situ SiN _x dielectric stacks for gate modulation in ultrathin-barrier AlGa _N /Ga _N MIS-HEMTs. , 2021, , .		2
23	Recent Progress on Perovskite Surfaces and Interfaces in Optoelectronic Devices. Advanced Materials, 2021, 33, e2006004.	21.0	86
24	Improvement of $\hat{\text{I}}^2\text{-Ga}_{2\text{O}_3}$ MIS-SBD Interface Using Al-Reacted Interfacial Layer. IEEE Transactions on Electron Devices, 2021, 68, 3314-3319.	3.0	4
25	Investigation on the release of residual stress in a folded structure applied to MEMS devices. Micro and Nano Letters, 2021, 16, 443-447.	1.3	0
26	Distinguishing various influences on the electrical properties of thin-barrier AlGa _N /Ga _N heterojunctions with in-situ SiN caps. Materials Science in Semiconductor Processing, 2021, 132, 105907.	4.0	6
27	A Miniature GaN Chip for Surface Roughness Measurement. IEEE Transactions on Electron Devices, 2021, 68, 4977-4981.	3.0	2
28	In situ characterization of buckling dynamics in silicon microribbon on an elastomer substrate. Extreme Mechanics Letters, 2021, 48, 101397.	4.1	1
29	Application of a gateless AlGa _N /Ga _N HEMT sensor for diesel soot particulate detection. Sensors and Actuators B: Chemical, 2021, 349, 130811.	7.8	3
30	High-temperature superconductivity in transition metallic hydrides MH ₁₁ (M = Mo, W, Nb,) T _j ETQq0 0.0 rgBT /Overlock 10	2.8	15
31	MiR-34c promotes hepatic stellate cell activation and Liver Fibrogenesis by suppressing ACSL1 expression. International Journal of Medical Sciences, 2021, 18, 615-625.	2.5	13
32	Fluid-injection-induced earthquakes characterized by hybrid-frequency waveforms manifest the transition from aseismic to seismic slip. Nature Communications, 2021, 12, 6862.	12.8	22
33	InAlN/GaN HEMTs on Si with $0.18 \hat{\text{I}} \hat{\text{O}} \hat{\text{A}} \hat{\text{m}} \text{m}$ Contact Resistance and 2.1-A/mm Drain Current Density. , 2021, , .		1
34	Ultra-Low Contact Resistivity of $\hat{\text{I}} \hat{\text{O}} \hat{\text{A}} \hat{\text{m}} \text{m}$ for Au-Free Ti _x Al _y Alloy Contact on Non-Recessed i-AlGa _N /Ga _N . IEEE Electron Device Letters, 2020, 41, 143-146.	3.9	24
35	Low leakage GaN HEMTs with sub-100Ånm T-shape gates fabricated by a low-damage etching process. Journal of Materials Science: Materials in Electronics, 2020, 31, 5886-5891.	2.2	1
36	Dual beam-shear differential interference microscopy for full-field surface deformation gradient characterization. Journal of the Mechanics and Physics of Solids, 2020, 145, 104162.	4.8	6

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37	Well Proximity Governing Stress Drop Variation and Seismic Attenuation Associated With Hydraulic Fracturing Induced Earthquakes. <i>Journal of Geophysical Research: Solid Earth</i> , 2020, 125, e2020JB020103.	3.4	23
38	Apatinib in patients with advanced chordoma: a single-arm, single-centre, phase 2 study. <i>Lancet Oncology</i> , The, 2020, 21, 1244-1252.	10.7	41
39	Myeloid-Derived Suppressor Cells Promote the Progression of Primary Membranous Nephropathy by Enhancing Th17 Response. <i>Frontiers in Immunology</i> , 2020, 11, 1777.	4.8	17
40	Very-Low Resistance Contact to 2D Electron Gas by Annealing Induced Penetration Without Spikes Using TaAl/Au on Non-Recessed i-AlGaIn/GaN. <i>IEEE Electron Device Letters</i> , 2020, 41, 1484-1487.	3.9	5
41	The Impact of Gate Recess on the H ₂ , Detection Properties of Pt-AlGaIn/GaN HEMT Sensors. <i>IEEE Sensors Journal</i> , 2020, 20, 8947-8955.	4.7	17
42	A Study on the Largest Hydraulic-Fracturing-Induced Earthquake in Canada: Observations and Static Stress-Drop Estimation. <i>Bulletin of the Seismological Society of America</i> , 2020, 110, 2283-2294.	2.3	30
43	High performance of La-doped Y2O3 transparent ceramics. <i>Journal of Advanced Ceramics</i> , 2020, 9, 493-502.	17.4	33
44	Gate Leakage Suppression and Breakdown Voltage Enhancement in p-GaN HEMTs Using Metal/Graphene Gates. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 875-880.	3.0	25
45	Dual-Mode Hybrid Quasi-SAW/BAW Resonators With High Effective Coupling Coefficient. <i>IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control</i> , 2020, 67, 1916-1921.	3.0	7
46	Low-Dimensional Contact Layers for Enhanced Perovskite Photodiodes. <i>Advanced Functional Materials</i> , 2020, 30, 2001692.	14.9	30
47	Oxygen-based digital etching of AlGaIn/GaN structures with AlN as etch-stop layers. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2019, 37, .	2.1	15
48	A new wet etching method for black phosphorus layer number engineering: experiment, modeling and DFT simulations. , 2019, , .		0
49	Blue cooperative up-conversion luminescence of Yb:Y2O3 transparent ceramics. <i>Ceramics International</i> , 2019, 45, 9278-9282.	4.8	11
50	Ab initio studies of copper hydrides under high pressure. <i>Frontiers of Physics</i> , 2019, 14, 1.	5.0	9
51	Enhanced dielectric properties of BaTiO3 based on ultrafine powders by two-step calcination. <i>Physica B: Condensed Matter</i> , 2019, 560, 155-161.	2.7	17
52	EWS-FLI1-mediated tenascin-C expression promotes tumour progression by targeting MALAT1 through integrin $\alpha 5 \beta 1$ -mediated YAP activation in Ewing sarcoma. <i>British Journal of Cancer</i> , 2019, 121, 922-933.	6.4	30
53	Ab Initio Approach and Its Impact on Superconductivity. <i>Journal of Superconductivity and Novel Magnetism</i> , 2019, 32, 53-60.	1.8	29
54	Impact of high temperature H2 pre-treatment on Pt-AlGaIn/GaN HEMT sensor for H2S detection. <i>Sensors and Actuators B: Chemical</i> , 2019, 280, 138-143.	7.8	22

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55	Investigation of Band Alignment for Hybrid 2D-MoS ₂ /3D-Î ² -Ga ₂ O ₃ Heterojunctions with Nitridation. Nanoscale Research Letters, 2019, 14, 360.	5.7	10
56	Evaluation of LPCVD SiN_{<i>x</i>} Gate Dielectric Reliability by TDDB Measurement in Si-Substrate-Based AlGaIn/GaN MIS-HEMT. IEEE Transactions on Electron Devices, 2018, 65, 1759-1764.	3.0	23
57	High-Pressure Formation of Cobalt Polyhydrides: A First-Principle Study. Inorganic Chemistry, 2018, 57, 181-186.	4.0	22
58	Impact of Preoperative Hepatitis B Virus Levels on Prognosis After Primary and Repeat Hepatectomies for Hepatocellular Carcinoma Patientsâ€”a Retrospective Study. Journal of Gastrointestinal Surgery, 2018, 22, 872-883.	1.7	5
59	A simulation study of field plate termination in Ga ₂ O ₃ Schottky barrier diodes. Chinese Physics B, 2018, 27, 127302.	1.4	9
60	Recent Advances in Î ² -Ga ₂ O ₃ â€”Metal Contacts. Nanoscale Research Letters, 2018, 13, 246.	5.7	76
61	AlGaIn/GaN HEMT micro-sensor technology for gas sensing applications. , 2018, , .		4
62	A Comprehensive Review of Recent Progress on GaN High Electron Mobility Transistors: Devices, Fabrication and Reliability. Electronics (Switzerland), 2018, 7, 377.	3.1	109
63	Band alignment of indiumâ€”galliumâ€”zinc oxide/Î ² -Ga₂O₃ \$(ar{2}01)\$ heterojunction determined by angle-resolved X-ray photoelectron spectroscopy. Japanese Journal of Applied Physics, 2018, 57, 100312.	1.5	9
64	Au-based and Au-free ohmic contacts to AlGaIn/GaN structures on silicon or Sapphire substrates. , 2018, , .		0
65	Hydrogen sulfide detection properties of Pt-gated AlGaIn/GaN HEMT-sensor. Sensors and Actuators B: Chemical, 2018, 274, 636-644.	7.8	24
66	System in package (SiP) technology: fundamentals, design and applications. Microelectronics International, 2018, 35, 231-243.	0.6	14
67	Chronic Liver Injury Induces Conversion of Biliary Epithelial Cells into Hepatocytes. Cell Stem Cell, 2018, 23, 114-122.e3.	11.1	197
68	Investigation of AlGaIn/GaN HEMTs degradation with gate pulse stressing at cryogenic temperature. AIP Advances, 2017, 7, .	1.3	5
69	Study of the enhancement-mode AlGaIn/GaN high electron mobility transistor with split floating gates. Solid-State Electronics, 2017, 137, 52-57.	1.4	2
70	A novel enhancement mode AlGaIn/GaN high electron mobility transistor with split floating gates. Chinese Physics B, 2017, 26, 047305.	1.4	3
71	Influence of feedstock concentration on tetragonality and particle size of hydrothermally synthesized barium titanate powders. Ceramics International, 2017, 43, 14813-14817.	4.8	7
72	Volume-based predictive biomarkers of sequential FDG-PET/CT for sunitinib in cancer of unknown primary: identification of the best benefited patients. European Journal of Nuclear Medicine and Molecular Imaging, 2017, 44, 199-205.	6.4	4

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73	Patient-oncologist alliance and psychosocial well-being in Chinese society strongly affect cancer management adherence with cancer of unknown primary. <i>Psycho-Oncology</i> , 2017, 26, 991-998.	2.3	3
74	The enhancement mode AlGaIn/GaN high electron mobility transistor based on charge storage. , 2017, , .		0
75	Pt-AlGaIn/GaN HEMT-sensor layout optimization for enhancement of hydrogen detection. , 2017, , .		1
76	Pt-AlGaIn/GaN HEMT-Sensor for Hydrogen Sulfide (H ₂ S) Detection. <i>Proceedings (mdpi)</i> , 2017, 1, .	0.2	3
77	microRNA-625 inhibits tumorigenicity by suppressing proliferation, migration and invasion in malignant melanoma. <i>Oncotarget</i> , 2017, 8, 13253-13263.	1.8	34
78	Potentials of the elevated circulating miR-185 level as a biomarker for early diagnosis of HBV-related liver fibrosis. <i>Scientific Reports</i> , 2016, 6, 34157.	3.3	18
79	Trap behaviours characterization of AlGaIn/GaN high electron mobility transistors by room-temperature transient capacitance measurement. <i>AIP Advances</i> , 2016, 6, 095021.	1.3	11
80	Oxide-based analog synapse: Physical modeling, experimental characterization, and optimization. , 2016, , .		19
81	Seismicity along St. Lawrence Paleorift Faults Overprinted by a Meteorite Impact Structure in Charlevoix, Québec, Eastern Canada. <i>Bulletin of the Seismological Society of America</i> , 2016, 106, 2663-2673.	2.3	16
82	Preparation of Aluminum Nanomesh Thin Films from an Anodic Aluminum Oxide Template as Transparent Conductive Electrodes. <i>Scientific Reports</i> , 2016, 6, 20114.	3.3	25
83	Development of three-dimensional memory (3D-M). <i>Proceedings of SPIE</i> , 2016, , .	0.8	0
84	A novel enhance-mode AlGaIn/GaN HEMT with split floating gates. , 2016, , .		0
85	Si/PEDOT:PSS hybrid solar cells incorporated with silver plasmonic nanospheres. <i>Thin Solid Films</i> , 2016, 599, 37-41.	1.8	2
86	Pilocytopoid astrocytomas with rare rosenthal fibers. <i>Brain Tumor Pathology</i> , 2016, 33, 35-39.	1.7	3
87	Stress adjustment revealed by seismicity and earthquake focal mechanisms in northeast China before and after the 2011 Tohoku-Oki earthquake. <i>Tectonophysics</i> , 2016, 666, 23-32.	2.2	18
88	Pressure-induced decomposition of solid hydrogen sulfide. <i>Physical Review B</i> , 2015, 91, .	3.2	255
89	The role of the miR-31/FIH1 pathway in TGF- β -induced liver fibrosis. <i>Clinical Science</i> , 2015, 129, 305-317.	4.3	48
90	Isolated cases of remote dynamic triggering in Canada detected using cataloged earthquakes combined with a matched-filter approach. <i>Geophysical Research Letters</i> , 2015, 42, 5187-5196.	4.0	35

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91	Planar Bulk MOSFETs With Self-Aligned Pocket Well to Improve Short-Channel Effects and Enhance Device Performance. IEEE Transactions on Electron Devices, 2015, 62, 1411-1418.	3.0	12
92	Overshoot Stress on Ultra-Thin HfO ₂ High-κ Layer and Its Impact on Lifetime Extraction. IEEE Electron Device Letters, 2015, 36, 1267-1270.	3.9	4
93	miR-27a suppresses the clonogenic growth and migration of human glioblastoma multiforme cells by targeting BTG2. International Journal of Oncology, 2015, 46, 1601-1608.	3.3	16
94	A new computational model for human thyroid cancer enhances the preoperative diagnostic efficacy. Oncotarget, 2015, 6, 28463-28477.	1.8	10
95	Simulated optical absorption enhancement in random silicon nanohole structure for solar cell application. Journal of Applied Physics, 2014, 116, .	2.5	9
96	Imaging findings of cryptococcal infection of the thoracic spine. International Journal of Infectious Diseases, 2014, 29, 162-165.	3.3	14
97	Shallow junction and contact realization by diffusion of heavily doped polycrystalline-germanium for Ge devices. , 2014, , .		0
98	High efficiency silicon nanohole/organic heterojunction hybrid solar cell. Applied Physics Letters, 2014, 104, 053104.	3.3	30
99	Optical absorption enhancement in a Si nanohole structure with hexagonal unit cell for solar cell application. Nanotechnology, 2014, 25, 415303.	2.6	4
100	Light trapping in hybrid nanopyramid and nanohole structure silicon solar cell beyond the Lambertian limit. Journal of Applied Physics, 2014, 116, 074310.	2.5	9
101	Higher LRRFIP1 expression in glioblastoma multiforme is associated with better response to teniposide, a type II topoisomerase inhibitor. Biochemical and Biophysical Research Communications, 2014, 446, 1261-1267.	2.1	11
102	A Novel Defect-Engineering-Based Implementation for High-Performance Multilevel Data Storage in Resistive Switching Memory. IEEE Transactions on Electron Devices, 2013, 60, 1379-1383.	3.0	48
103	A Study on Grapheneâ€”Metal Contact. Crystals, 2013, 3, 257-274.	2.2	61
104	Design guideline of Si nanohole/PEDOT:PSS hybrid structure for solar cell application. Nanotechnology, 2013, 24, 355301.	2.6	15
105	Design guidelines for slanting silicon nanowire arrays for solar cell application. Journal of Applied Physics, 2013, 114, .	2.5	29
106	Design guidelines for (111) Si inclined nanohole arrays in thin film solar cells. , 2013, , .		0
107	The transport properties of oxygen vacancy-related polaron-like bound state in HfOx. Scientific Reports, 2013, 3, 3246.	3.3	17
108	A Low Energy Oxideâ€”Based Electronic Synaptic Device for Neuromorphic Visual Systems with Tolerance to Device Variation. Advanced Materials, 2013, 25, 1774-1779.	21.0	445

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109	Stochastic learning in oxide binary synaptic device for neuromorphic computing. <i>Frontiers in Neuroscience</i> , 2013, 7, 186.	2.8	129
110	Surface Nanostructure Optimization for GaAs Solar Cell Application. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 10ND13.	1.5	2
111	Design principles for plasmonic thin film GaAs solar cells with high absorption enhancement. <i>Journal of Applied Physics</i> , 2012, 112, 054326.	2.5	33
112	Crystallization and surface texturing of amorphous-Si induced by UV laser for photovoltaic application. <i>Journal of Applied Physics</i> , 2012, 111, .	2.5	16
113	Solar energy harnessing in hexagonally arranged Si nanowire arrays and effects of array symmetry on optical characteristics. <i>Nanotechnology</i> , 2012, 23, 194010.	2.6	48
114	Transport properties of HfO ₂ -based resistive-switching memories. <i>Physical Review B</i> , 2012, 85, .	3.2	51
115	Perspective of flash memory realized on vertical Si nanowires. <i>Microelectronics Reliability</i> , 2012, 52, 651-661.	1.7	7
116	Novel low aspect-ratio Si nano-hemisphere array surface texture application to ultrathin film solar cells. , 2011, , .		1
117	Modeling of Retention Failure Behavior in Bipolar Oxide-Based Resistive Switching Memory. <i>IEEE Electron Device Letters</i> , 2011, 32, 276-278.	3.9	61
118	Surface plasmon enhanced light absorption for thin film poly-silicon solar cell with hybrid structure and metal alloy nano-particles. , 2011, , .		1
119	Aligned Si nanowire-based solar cells. <i>Nanoscale</i> , 2011, 3, 4888.	5.6	44
120	Design guideline of high efficiency crystalline Si thin film solar cell with nanohole array textured surface. <i>Journal of Applied Physics</i> , 2011, 109, .	2.5	47
121	Low aspect-ratio hemispherical nanopit surface texturing for enhancing light absorption in crystalline Si thin film-based solar cells. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	68
122	Optical simulation of low aspect ratio hemisphere array surface texturing for crystalline Si film solar cells. <i>Energy Procedia</i> , 2011, 8, 180-184.	1.8	5
123	Enhancement of Si-Based Solar Cell Efficiency via Nanostructure Integration. <i>Green Energy and Technology</i> , 2011, , 3-55.	0.6	0
124	The miR-34 family is upregulated and targets ACSL1 in dimethylnitrosamine-induced hepatic fibrosis in rats. <i>FEBS Journal</i> , 2011, 278, 1522-1532.	4.7	115
125	Multideposition Multiroom-Temperature Annealing via Ultraviolet Ozone for HfZrO High- κ and Integration With a TiN Metal Gate in a Gate-Last Process. <i>IEEE Transactions on Electron Devices</i> , 2011, 58, 2177-2181.	3.0	13
126	Novel Silicon Nanohemisphere Array Solar Cells with Enhanced Performance. <i>Small</i> , 2011, 7, 3138-3143.	10.0	50

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127	Solar Cells: Novel Silicon Nanohemisphere-Array Solar Cells with Enhanced Performance (Small) Tj ETQq1 1 0.784314 rgBT /Overlock 10	10.6	0
128	Periodic silicon nanocone arrays with controllable dimensions prepared by two-step etching using nanosphere lithography and NH_4OH solution. Solid State Communications, 2011, 151, 127-129.	1.9	12
129	Band structures and optical gain of strained GaAs _x P _{1-x} /GaP quantum wells. Applied Physics Letters, 2011, 98, 121112.	3.3	7
130	Enhanced Si thin film solar cells short-circuit current with rational-designed Si nano-pillar array surface texturing. , 2011, , .		0
131	Periodically Aligned Si Nanopillar Arrays as Efficient Antireflection Layers for Solar Cell Applications. Nanoscale Research Letters, 2010, 5, 1721-1726.	5.7	60
132	Si nanocone array optimization on crystalline Si thin films for solar energy harvesting. Journal Physics D: Applied Physics, 2010, 43, 255101.	2.8	43
133	Surface texturing of Si thin film solar cells via low cost periodic nanopillars array to enhance efficiency. , 2010, , .		0
134	Highly conductive aligned carbon film for interconnect application. , 2010, , .		0
135	Fabrication and SERS Performance of Silver-Nanoparticle-Decorated Si/ZnO Nanotrees in Ordered Arrays. ACS Applied Materials & Interfaces, 2010, 2, 1824-1828.	8.0	198
136	Optical absorption enhancement in nanopore textured-silicon thin film for photovoltaic application. Optics Letters, 2010, 35, 40.	3.3	64
137	Periodic silicon nanocones arrays with controllable dimensions prepared by two-step etching using nanosphere lithography and NH_4OH solution. , 2010, , .		0
138	Si nanopillar array optimization on Si thin films for solar energy harvesting. Applied Physics Letters, 2009, 95, .	3.3	245
139	Design guidelines of periodic Si nanowire arrays for solar cell application. Applied Physics Letters, 2009, 95, .	3.3	167
140	Enhancement of the Flatband Modulation of Ni-Silicided Gates on Hf-Based Dielectrics. IEEE Transactions on Electron Devices, 2008, 55, 2238-2245.	3.0	5
141	Work-Function Engineering for 32-nm-Node pMOS Devices: High-Performance TaCNO-Gated Films. IEEE Electron Device Letters, 2008, 29, 1203-1205.	3.9	5
142	Monte Carlo Simulation of p- and n-channel GOI MOSFETs by Solving the Quantum Boltzmann Equation. IEEE Transactions on Electron Devices, 2005, 52, 2258-2264.	3.0	31
143	Thermally Robust HfN Metal as a Promising Gate Electrode for Advanced MOS Device Applications. IEEE Transactions on Electron Devices, 2004, 51, 609-615.	3.0	57
144	SIMS study on N diffusion in hafnium oxynitride. Applied Surface Science, 2004, 231-232, 590-593.	6.1	7

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145	Dependence of Chemical Composition Ratio on Electrical Properties of HfO ₂ -Al ₂ O ₃ Gate Dielectric. Japanese Journal of Applied Physics, 2003, 42, L220-L222.	1.5	13
146	Investigation of hole-tunneling current through ultrathin oxynitride/oxide stack gate dielectrics in p-MOSFETs. IEEE Transactions on Electron Devices, 2002, 49, 1158-1164.	3.0	42